PEMB14; PUMB14 PNP/PNP resistor-equipped transistors; R1 = 47 kΩ, R2 = open

Rev. 02 — 31 August 2009

Product data sheet

1. Product profile

1.1 General description

PNP/PNP resistor-equipped transistors

Table 1	Produ	ct overview
10010		

Type number	Package		NPN/PNP	NPN/NPN	
	NXP	JEITA	complement	complement	
PEMB14	SOT666	-	PEMD14	PEMH14	
PUMB14	SOT363	SC-88	PUMD14	PUMH14	

1.2 Features

- Built-in bias resistors
- Simplifies circuit design
- Reduces component count
- Reduces pick and place cost

1.3 Applications

- Low current peripheral driver
- Control of IC inputs
- Replacement of general-purpose transistors in digital applications

1.4 Quick reference data

Table 2. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{CEO}	collector-emitter voltage	open base	-	-	-50	V
lo	output current (DC)		-	-	-100	mA
R1	bias resistor 1 (input)		33	47	61	kΩ



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006aaa268

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2. Pinning information

Table 3.	Pinning					
Pin	Description	Simplified outline	Symbol			
1	GND (emitter) TR1					
2	input (base) TR1	6 5 4				
3	output (collector) TR2		TR1 TR1 TR2			
4	GND (emitter) TR2					
5	input (base) TR2					
6	output (collector) TR1	001aab555	R1			

3. Ordering information

Table 4.	Ordering	information
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Type number	Package				
	Name	Description	Version		
PEMB14	-	plastic surface mounted package; 6 leads	SOT666		
PUMB14	SC-88	plastic surface mounted package; 6 leads	SOT363		

4. Marking

Table 5. Marking codes	
Type number	Marking code ^[1]
PEMB14	5A
PUMB14	T1*

[1] * = -: made in Hong Kong

* = p: made in Hong Kong

* = t: made in Malaysia

* = W: made in China

PEMB14; PUMB14

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5. Limiting values

Symbol	Parameter	Conditions	Min	Max	Unit
Per transis	stor				
V _{CBO}	collector-base voltage	open emitter	-	-50	V
V _{CEO}	collector-emitter voltage	open base	-	-50	V
V _{EBO}	emitter-base voltage	open collector	-	-5	V
lo	output current (DC)		-	-100	mA
I _{CM}	peak collector current		-	-100	mA
P _{tot}	total power dissipation	$T_{amb} \le 25 \ ^{\circ}C$			
	SOT363		<u>[1]</u> -	200	mW
	SOT666		<u>[1] [2]</u> _	200	mW
T _{stg}	storage temperature		-65	+150	°C
Tj	junction temperature		-	150	°C
T _{amb}	ambient temperature		-65	+150	°C
Per device)				
P _{tot}	total power dissipation	$T_{amb} \le 25 \ ^{\circ}C$			
	SOT363		<u>[1]</u> _	300	mW
	SOT666		<u>[1] [2]</u>	300	mW

[1] Device mounted on a FR4 printed-circuit board, single-sided copper, tin-plated and standard footprint.

[2] Reflow soldering is the only recommended soldering method.

6. Thermal characteristics

Table 7.	Thermal characteristics					
Symbol	Parameter	Conditions	Min	Тур	Мах	Unit
Per trans	istor					
R _{th(j-a)}	thermal resistance from junction to ambient	$T_{amb} \le 25 \ ^{\circ}C$				
	SOT363		<u>[1]</u> -	-	625	K/W
	SOT666		<u>[1] [2]</u> _	-	625	K/W
Per devic	e					
R _{th(j-a)}	thermal resistance from junction to ambient	$T_{amb} \le 25 \ ^{\circ}C$				
	SOT363		<u>[1]</u> -	-	416	K/W
	SOT666		<u>[1]</u> <u>[2]</u> _	-	416	K/W

[1] Device mounted on a FR4 printed-circuit board, single-sided copper, tin-plated and standard footprint.

[2] Reflow soldering is the only recommended soldering method.

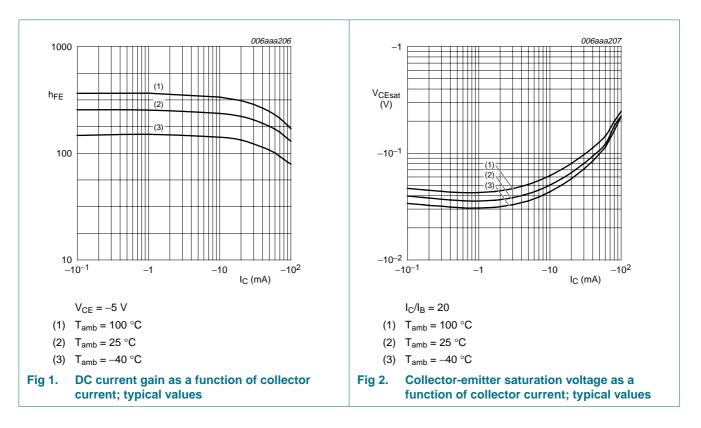
PNP/PNP resistor-equipped transistors; R1 = 47 kΩ, R2 = open

7. Characteristics

Table 8. Characteristics

T_{amb} = 25 °C unless otherwise specified

0			64	-		
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Per transis	stor					
I _{CBO}	collector-base cut-off current	$V_{CB} = -50 \text{ V}; I_E = 0 \text{ A}$	-	-	-100	nA
I _{CEO}	collector-emitter	$V_{CE} = -30 \text{ V}; \text{ I}_{B} = 0 \text{ A}$	-	-	-1	μA
	cut-off current	$V_{CE} = -30 \text{ V}; I_B = 0 \text{ A};$ T _j = 150 °C	-	-	-50	μA
I _{EBO}	emitter-base cut-off current	$V_{EB} = -5 \text{ V}; \text{ I}_{C} = 0 \text{ A}$	-	-	-100	nA
h _{FE}	DC current gain	$V_{CE} = -5 \text{ V}; \text{ I}_{C} = -1 \text{ mA}$	100	-	-	
V _{CEsat}	collector-emitter saturation voltage	$I_{C} = -10$ mA; $I_{B} = -0.5$ mA	-	-	-150	mV
R1	bias resistor 1 (input)		33	47	61	kΩ
C _c	collector capacitance	$\label{eq:VCB} \begin{array}{l} V_{CB} = -10 \text{ V}; \text{ I}_{E} = \text{i}_{e} = 0 \text{ A}; \\ \text{f} = 1 \text{ MHz} \end{array}$	-	-	2.5	pF



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8. Package outline

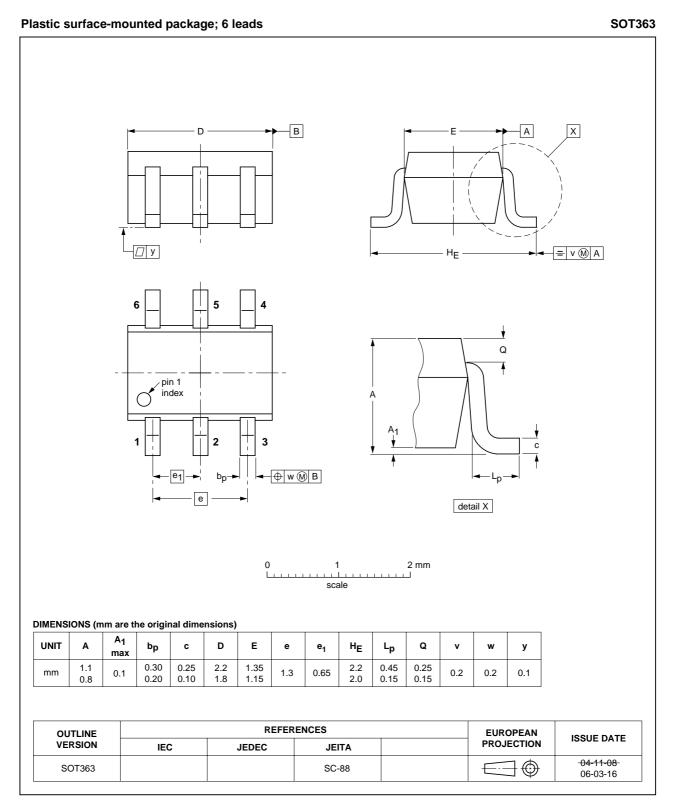


Fig 3. Package outline SOT363 (SC-88)

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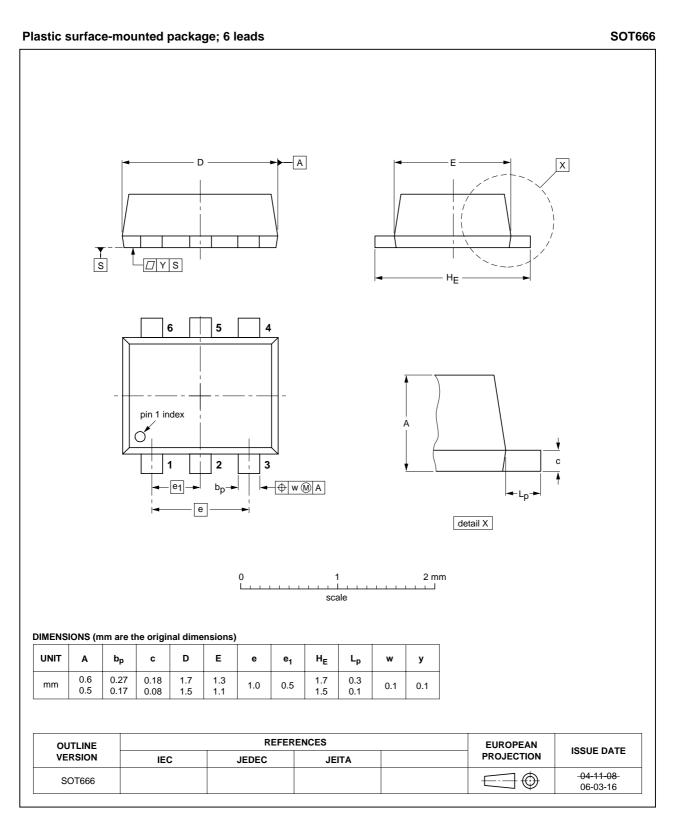


Fig 4. Package outline SOT666

PNP/PNP resistor-equipped transistors; R1 = 47 kΩ, R2 = open

9. Packing information

Table 9. Packing methods

The indicated -xxx are the last three digits of the 12NC ordering code. [1]

Type number	Package	Description	Packing q	uantity	
			3000	4000	10000
PEMB14	SOT666	4 mm pitch, 8 mm tape and reel;	-	-115	-
PUMB14	SOT363	4 mm pitch, 8 mm tape and reel; T1	^[2] -115	-	-135
PUMB14	SOT363	4 mm pitch, 8 mm tape and reel; T2	<u>3</u> -125	-	-165

[1] For further information and the availability of packing methods, see Section 12.

[2] T1: normal taping

[3] T2: reverse taping

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10. Revision history

Table 10. Revision histo	ory			
Document ID	Release date	Data sheet status	Change notice	Supersedes
PEMB14_PUMB14_2	20090831	Product data sheet	-	PEMB14_PUMB14_1
Modifications:		was changed to reflect the egal definitions and disclair		
	 Figure 3 "Packa 	age outline SOT363 (SC-88	3)": updated	
	Figure 4 "Packa	age outline SOT666": upda	ted	
PEMB14_PUMB14_1	20050217	Product data sheet	-	-

11. Legal information

11.1 Data sheet status

Document status ^{[1][2]}	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

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